

IGBT - Field Stop, Trench

650 V, 75 A

FGH75T65SQDT

Description

Using novel field stop IGBT technology, ON Semiconductor's new series of field stop 4th generation IGBTs offer the optimum performance for solar inverter, UPS, welder, telecom, ESS and PFC applications where low conduction and switching losses are essential.

Features

- Max Junction Temperature $T_J = 175^\circ\text{C}$
- Positive Temperature Co-efficient for Easy Parallel Operating
- High Current Capability
- Low Saturation Voltage: $V_{CE(sat)} = 1.6\text{ V (Typ.) @ } I_C = 75\text{ A}$
- 100% of the Parts Tested for I_{LM}
- High Input Impedance
- Fast Switching
- Tighten Parameter Distribution
- This Device is Pb-Free and is RoHS Compliant

Applications

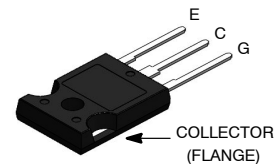
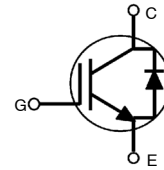
- Solar Inverter, UPS, Welder, Telecom, ESS, PFC



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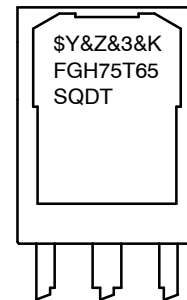
www.onsemi.com

V_{CES}	I_C
650 V	75 A



**TO-247-3LD
CASE 340CH**

MARKING DIAGRAM



- | | |
|--------------|-------------------------|
| \$Y | = ON Semiconductor Logo |
| &Z | = Assembly Plant Code |
| &3 | = Numeric Date Code |
| &K | = Lot Code |
| FGH75T65SQDT | = Specific Device Code |

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FGH75T65SQDT

ABSOLUTE MAXIMUM RATINGS

Symbol	Description	FGH50T65SQD-F155	Unit
V_{CES}	Collector to Emitter Voltage	650	V
V_{GES}	Gate to Emitter Voltage	± 20	V
	Transient Gate to Emitter Voltage	± 30	V
I_C	Collector Current	$T_C = 25^\circ\text{C}$	150
		$T_C = 100^\circ\text{C}$	75
I_{LM} (Note 1)	Pulsed Collector Current	$T_C = 25^\circ\text{C}$	300
I_{CM} (Note 2)	Pulsed Collector Current		300
I_F	Diode Forward Current	$T_C = 25^\circ\text{C}$	150
		$T_C = 100^\circ\text{C}$	75
I_{FM}	Pulsed Diode Maximum Forward Current	300	A
P_D	Maximum Power Dissipation	$T_C = 25^\circ\text{C}$	375
		$T_C = 100^\circ\text{C}$	188
T_J	Operating Junction Temperature	-55 to +175	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to +175	$^\circ\text{C}$
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. $V_{CC} = 400\text{ V}$, $V_{GE} = 15\text{ V}$, $I_C = 300\text{ A}$, $R_G = 21\ \Omega$, Inductive Load.
2. Repetitive rating: Pulse width limited by max. junction temperature.

THERMAL CHARACTERISTICS

Symbol	Parameter	FGH75T65SQDT-F155	Unit
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction to Case, Max.	0.4	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$ (Diode)	Thermal Resistance, Junction to Case, Max.	0.65	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	$^\circ\text{C}/\text{W}$

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Qty per Tube
FGH75T65SQDT-F155	FGH75T65SQDT	TO-247-3LD	Tube	-	-	30

FGH75T65SQDT

ELECTRICAL CHARACTERISTICS OF THE IGBT ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

BV_{CES}	Collector to Emitter Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	650	-	-	V
$\Delta BV_{CES} / \Delta T_J$	Temperature Coefficient of Breakdown Voltage	$I_C = 1\text{ mA}$, Reference to 25°C	-	0.6	-	V/ $^\circ\text{C}$
I_{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0\text{ V}$	-	-	250	μA
I_{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0\text{ V}$	-	-	± 400	nA

ON CHARACTERISTICS

$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 75\text{ mA}, V_{CE} = V_{GE}$	2.6	4.5	6.4	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 75\text{ A}, V_{GE} = 15\text{ V}, T_C = 25^\circ\text{C}$	-	1.6	2.1	V
		$I_C = 75\text{ A}, V_{GE} = 15\text{ V}, T_C = 175^\circ\text{C}$	-	1.92	-	V

DYNAMIC CHARACTERISTICS

C_{ies}	Input Capacitance	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	-	4845	-	pF
C_{oes}	Output Capacitance		-	155	-	pF
C_{res}	Reverse Transfer Capacitance		-	14	-	pF

SWITCHING CHARACTERISTICS

$T_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400\text{ V}, I_C = 18.8\text{ A}, R_G = 4.7\ \Omega, V_{GE} = 15\text{ V},$ Inductive Load, $T_C = 25^\circ\text{C}$	-	23	-	ns
T_r	Rise Time		-	10	-	ns
$T_{d(off)}$	Turn-Off Delay Time		-	120	-	ns
T_f	Fall Time		-	7	-	ns
E_{on}	Turn-On Switching Loss		-	300	-	μJ
E_{off}	Turn-Off Switching Loss		-	70	-	μJ
E_{ts}	Total Switching Loss		-	370	-	μJ
$T_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400\text{ V}, I_C = 37.5\text{ A}, R_G = 4.7\ \Omega, V_{GE} = 15\text{ V},$ Inductive Load, $T_C = 25^\circ\text{C}$	-	26	-	ns
T_r	Rise Time		-	19	-	ns
$T_{d(off)}$	Turn-Off Delay Time		-	114	-	ns
T_f	Fall Time		-	11	-	ns
E_{on}	Turn-On Switching Loss		-	746	-	μJ
E_{off}	Turn-Off Switching Loss		-	181	-	μJ
E_{ts}	Total Switching Loss		-	927	-	μJ
$T_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400\text{ V}, I_C = 18.5\text{ A}, R_G = 4.7\ \Omega, V_{GE} = 15\text{ V},$ Inductive Load, $T_C = 175^\circ\text{C}$	-	22	-	ns
T_r	Rise Time		-	12	-	ns
$T_{d(off)}$	Turn-Off Delay Time		-	135	-	ns
T_f	Fall Time		-	14	-	ns
E_{on}	Turn-On Switching Loss		-	760	-	μJ
E_{off}	Turn-Off Switching Loss		-	180	-	μJ
E_{ts}	Total Switching Loss		-	940	-	μJ

FGH75T65SQDT

ELECTRICAL CHARACTERISTICS OF THE IGBT ($T_C = 25^\circ\text{C}$ unless otherwise noted) (continued)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS						
$T_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400\text{ V}$, $I_C = 37.5\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GE} = 15\text{ V}$, Inductive Load, $T_C = 175^\circ\text{C}$	–	24	–	ns
T_r	Rise Time		–	24	–	ns
$T_{d(off)}$	Turn-Off Delay Time		–	125	–	ns
T_f	Fall Time		–	10	–	ns
E_{on}	Turn-On Switching Loss		–	1520	–	μJ
E_{off}	Turn-Off Switching Loss		–	401	–	μJ
E_{ts}	Total Switching Loss		–	1921	–	μJ
Q_g	Total Gate Charge	$V_{CE} = 400\text{ V}$, $I_C = 75\text{ A}$, $V_{GE} = 15\text{ V}$	–	128	–	nC
Q_{ge}	Gate to Emitter Charge		–	23	–	nC
Q_{gc}	Gate to Collector Charge		–	29	–	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ELECTRICAL CHARACTERISTICS OF THE DIODE ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit	
V_{FM}	Diode Forward Voltage	$I_F = 75\text{ A}$	$T_C = 25^\circ\text{C}$	–	1.8	2.1	V
			$T_C = 175^\circ\text{C}$	–	1.7	–	
E_{rec}	Reverse Recovery Energy	$I_F = 75\text{ A}$, $di_F/dt = 200\text{ A}/\mu\text{s}$	$T_C = 175^\circ\text{C}$	–	160	–	μJ
T_{rr}	Diode Reverse Recovery Time		$T_C = 25^\circ\text{C}$	–	76	–	ns
			$T_C = 175^\circ\text{C}$	–	270	–	
Q_{rr}	Diode Reverse Recovery Charge		$T_C = 25^\circ\text{C}$	–	206	–	nC
		$T_C = 175^\circ\text{C}$	–	2199	–		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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TYPICAL CHARACTERISTICS

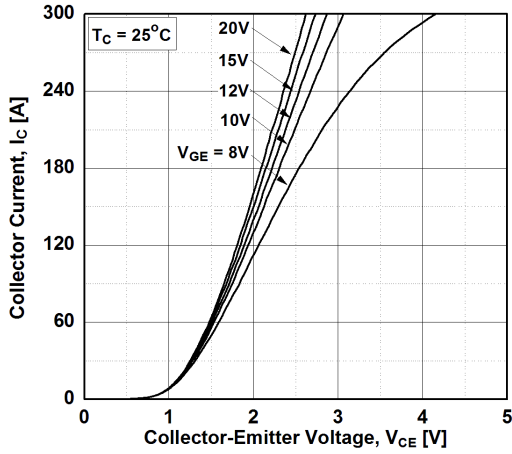


Figure 1. Typical Output Characteristics

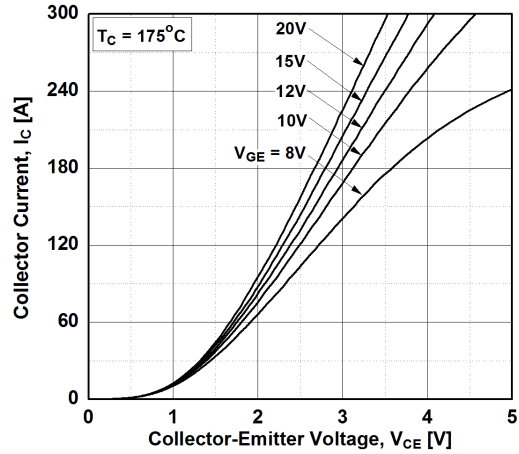


Figure 2. Typical Output Characteristics

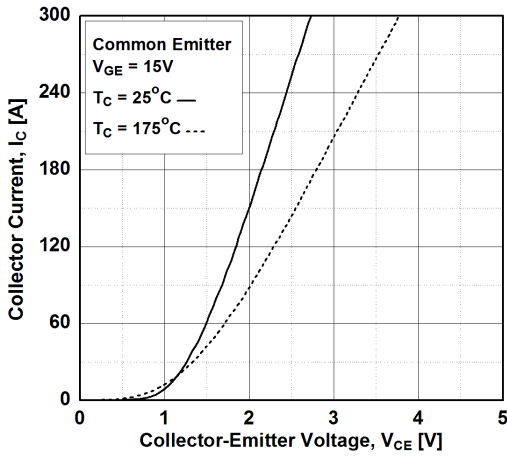


Figure 3. Typical Saturation Voltage Characteristics

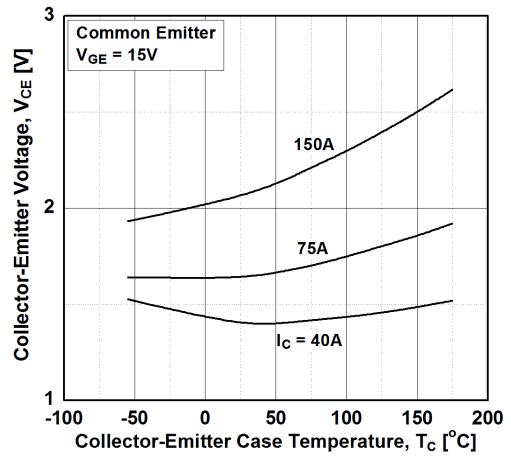


Figure 4. Saturation Voltage vs. Case Temperature at Variant Current Level

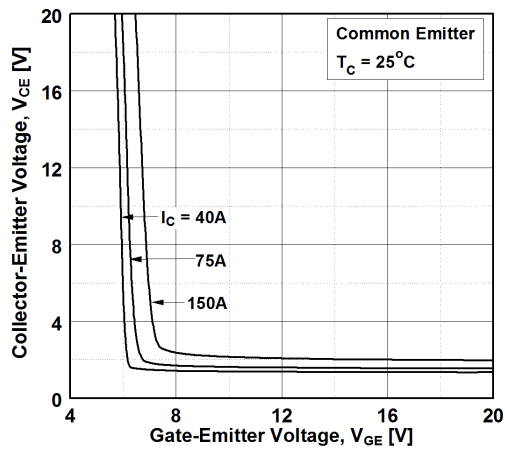


Figure 5. Saturation Voltage vs. V_{GE}

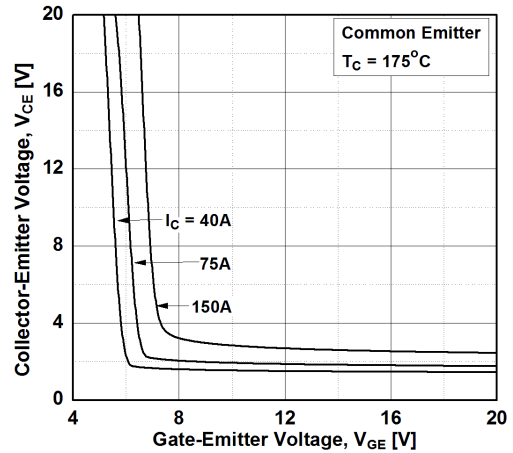


Figure 6. Saturation Voltage vs. V_{GE}

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TYPICAL CHARACTERISTICS (Continued)

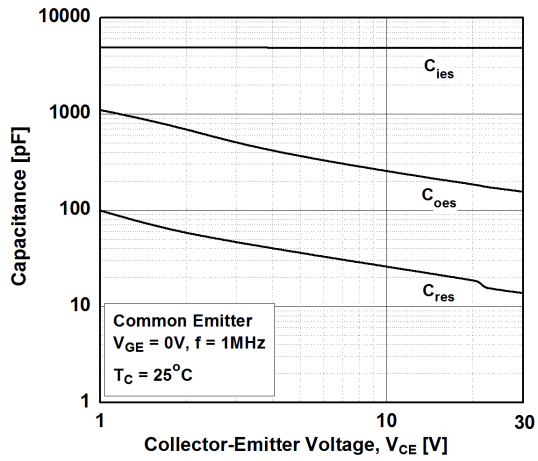


Figure 7. Capacitance Characteristics

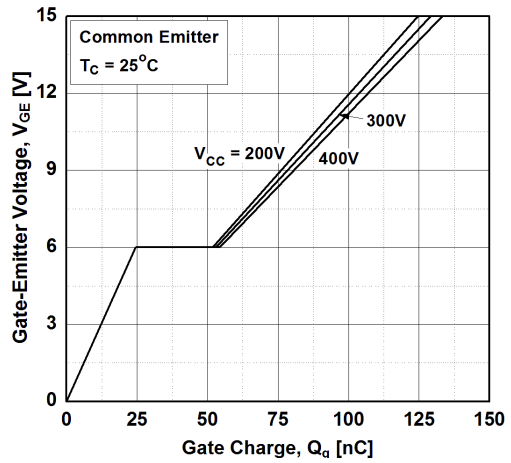


Figure 8. Gate Charge Characteristics

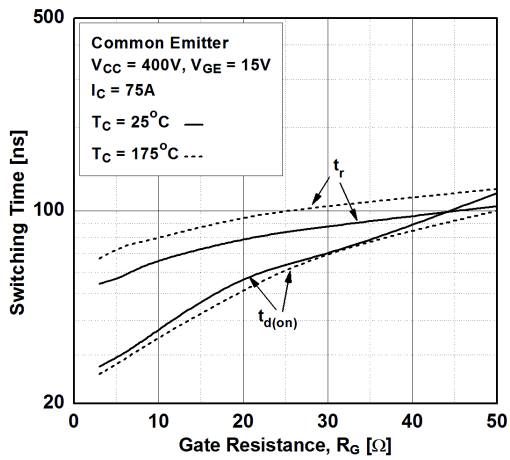


Figure 9. Turn-on Characteristics vs. Gate Resistance

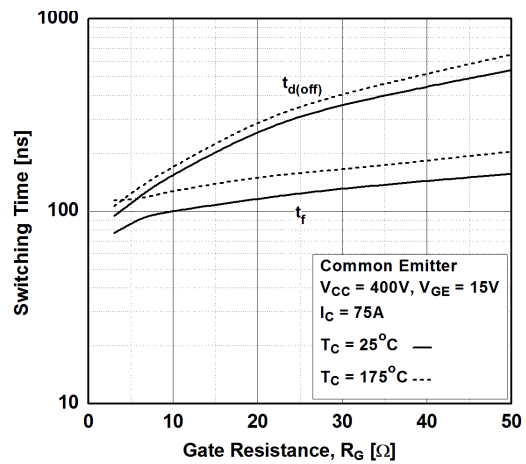


Figure 10. Turn-off Characteristics vs. Gate Resistance

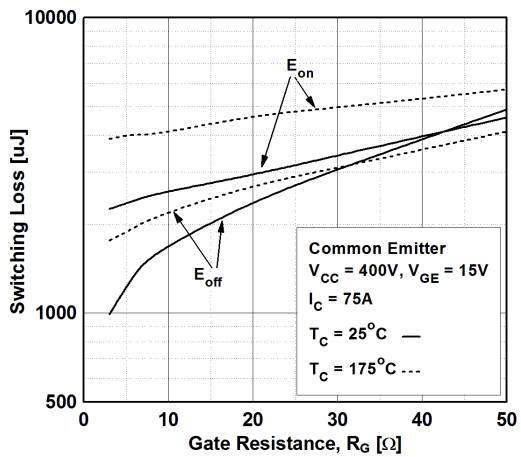


Figure 11. Switching Loss vs. Gate Resistance

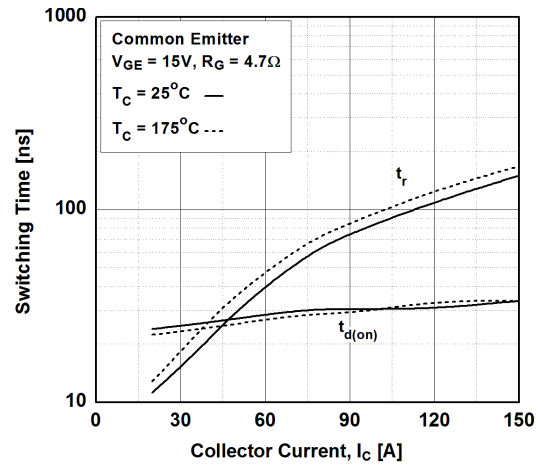


Figure 12. Turn-on Characteristics vs. Collector Current

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TYPICAL CHARACTERISTICS (Continued)

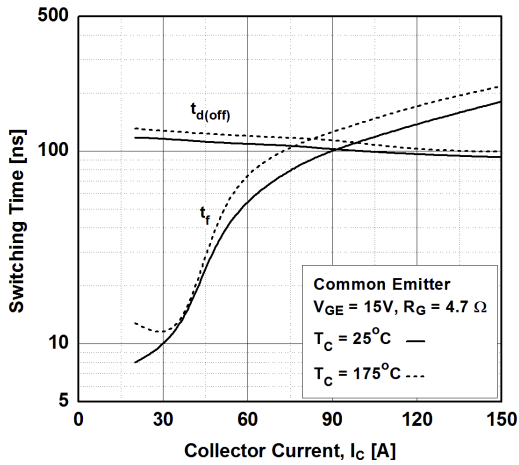


Figure 13. Turn-off Characteristics vs. Collector Current

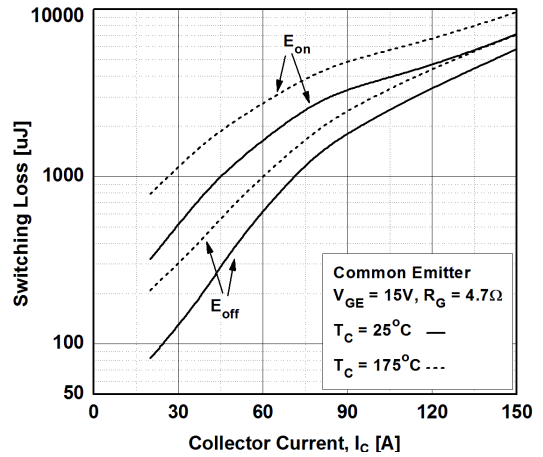


Figure 14. Switching Loss vs. Collector Current

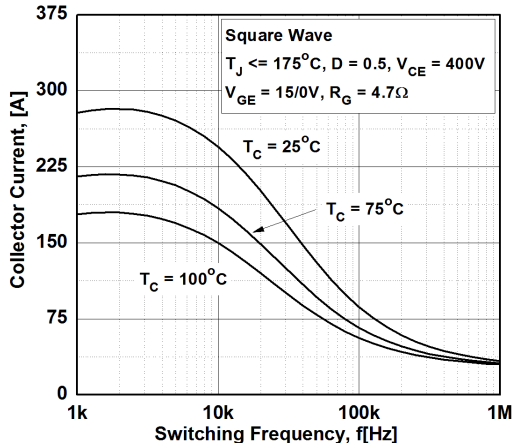


Figure 15. Load Current vs. Frequency

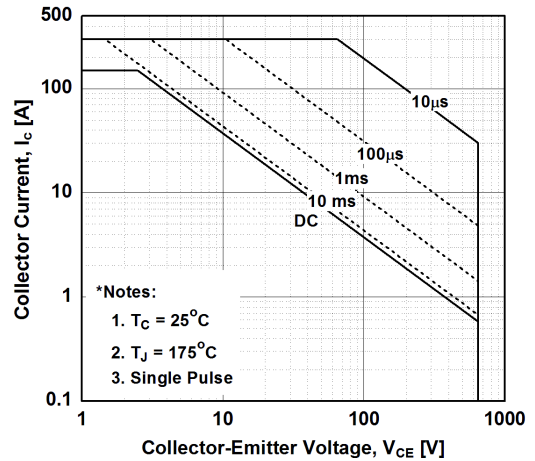


Figure 16. SOA Characteristics

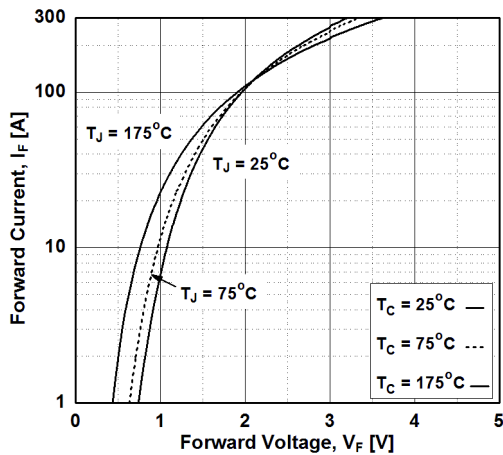


Figure 17. Forward Characteristics

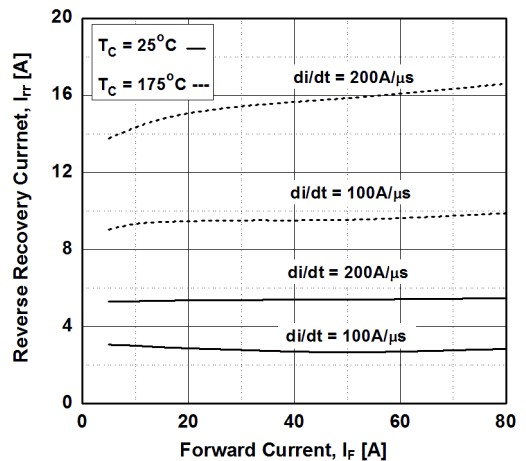


Figure 18. Reverse Recovery Current

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TYPICAL CHARACTERISTICS (Continued)

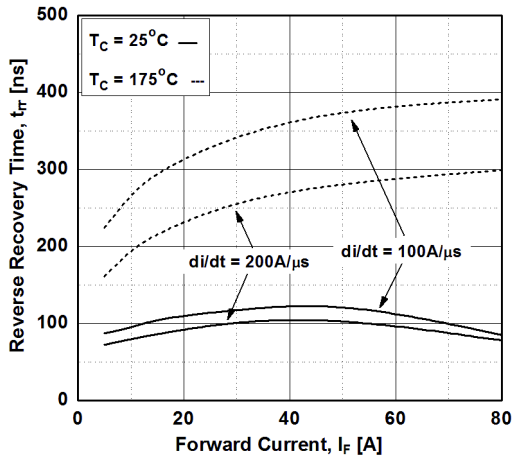


Figure 19. Reverse Recovery Time

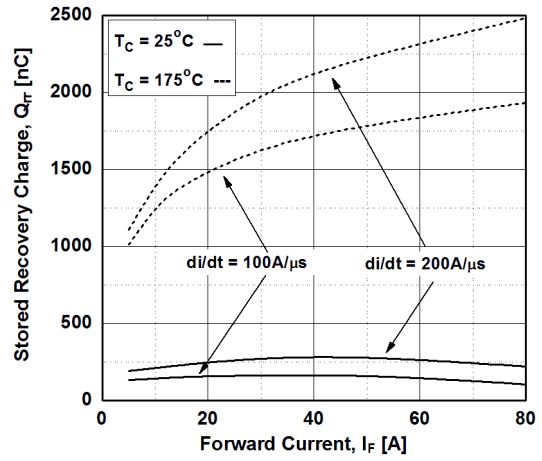


Figure 20. Stored Charge

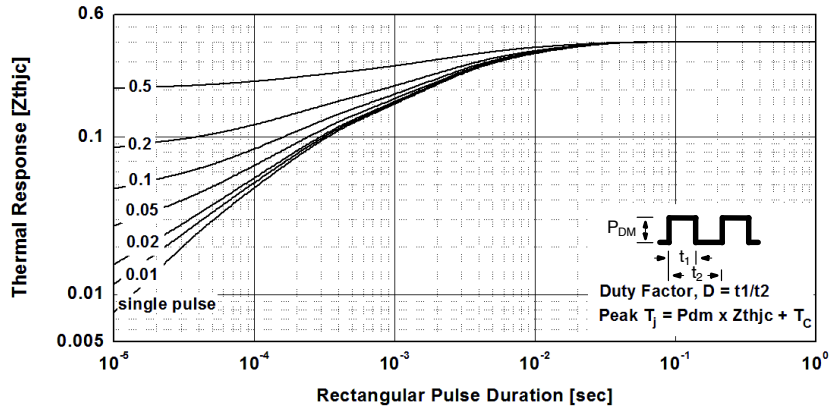


Figure 21. Transient Thermal Impedance of IGBT

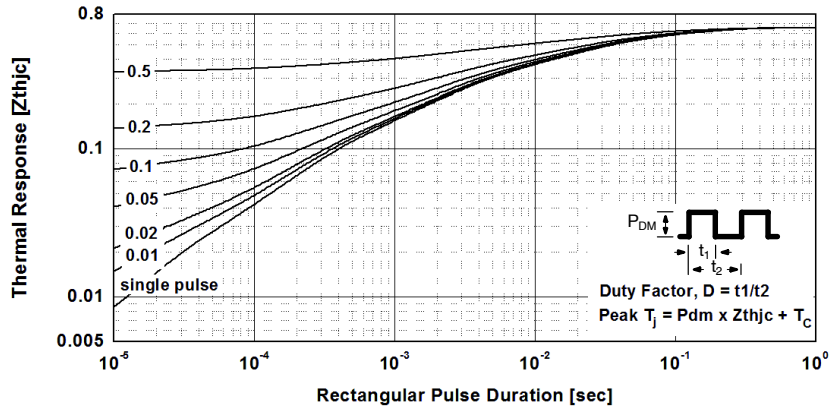


Figure 22. Transient Thermal Impedance of Diode

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

ON Semiconductor®



TO-247-3LD
CASE 340CH
ISSUE A

DATE 09 OCT 2019



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.29	2.475	2.66
A2	1.40	1.50	1.60
D	20.32	20.57	20.82
E	15.37	15.62	15.87
E2	4.96	5.08	5.20
e	~	5.56	~
L	19.75	20.00	20.25
L1	3.69	3.81	3.93
∅P	3.51	3.58	3.65
Q	5.34	5.46	5.58
S	5.34	5.46	5.58
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D1	13.08	~	~
D2	0.51	0.93	1.35
E1	12.81	~	~
∅P1	6.61	6.73	6.85

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